

S/N 09/866,938

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Wendell P. Noble et al.

Examiner: Jack Chen

Serial No.: 09/866,938

Group Art Unit: 2815

Filed: May 29, 2001

Docket: 303.330US3

Title: ULTRA HIGH DENSITY FLASH MEMORY

PATENT

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on October 4, 2002. Please amend the above-identified patent application as follows.

This response is accompanied by a Petition, as well as the appropriate fee, to obtain a one-month extension of the period for responding to the Office action, thereby moving the deadline for response from January 4, 2003 to February 4, 2003.

IN THE CLAIMS

02/12/2003 ASNITH 00000006 190743 09866938

01 FC:1202
02 FC:1201

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims

for the previously pending claim set. The substitute claim set is intended to reflect addition of new claims 70-76. The new claims are detailed below.

70. (New) A method comprising:

forming a first source/drain layer at a surface of a substrate;

forming a second source/drain layer at a surface of an epitaxial layer;

etching, in a first direction, a plurality of substantially parallel first troughs in the epitaxial layer;

forming a first gate dielectric layer along sidewall regions of the first troughs;

forming first floating gate regions along the sidewall regions of the first troughs and separated from the sidewall regions by the first gate dielectric layer, the first floating gate regions including a first conductive layer of N+ doped polysilicon;

forming first control gate regions between opposing first floating gate regions, the first control gate regions being separated from the first floating gate regions by a first intergate dielectric layer, and the first control gate regions including N+ doped polysilicon;

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